

CD4043B, CD4044B Types

CMOS Quad 3-State R/S Latches

High-Voltage Types (20-Volt Rating)
Quad NOR R/S Latch — CD4043B
Quad NAND R/S Latch — CD4044B

The RCA-CD4043B types are quad cross-coupled 3-state CMOS NOR latches and the CD4044B types are quad cross-coupled 3-state CMOS NAND latches. Each latch has a separate Q output and individual SET and RESET inputs. The Q outputs are controlled by a common ENABLE input. A logic "1" or high on the ENABLE input connects the latch states to the Q outputs. A logic "0" or low on the ENABLE input disconnects the latch states from the Q outputs, resulting in an open circuit condition on the Q outputs. The open circuit feature allows common busing of the outputs.

The CD4043B and CD4044B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), 16-lead ceramic flat packages (K suffix), and in chip form (H suffix).

- Features:
- 3-state outputs with common output ENABLE
 - Separate SET and RESET inputs for each latch
 - NOR and NAND configurations
 - 5-V, 10-V, and 15-V parametric ratings
 - Standardized symmetrical output characteristics
 - 100% tested for quiescent current at 20 V
 - Maximum input current of 1 μ A at 18 V over full package temperature range; 100 nA at 18 V and 25°C
 - Noise margin (over full package temperature range):
 - 1 V at $V_{DD} = 5$ V
 - 2 V at $V_{DD} = 10$ V
 - 2.5 V at $V_{DD} = 15$ V
 - Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"
- Applications:
- Holding register in multi-register system
 - Four bits of independent storage with output ENABLE
 - Strobed register
 - General digital logic
 - CD4043B for positive logic systems
 - CD4044B for negative logic systems

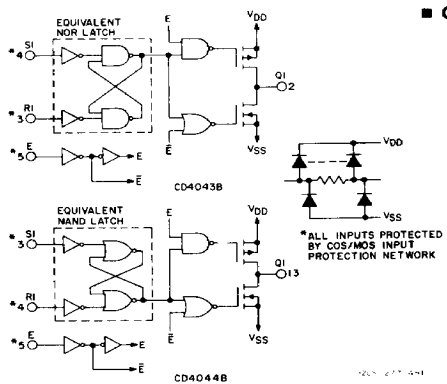
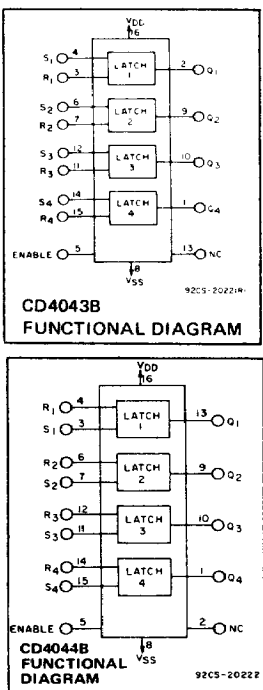
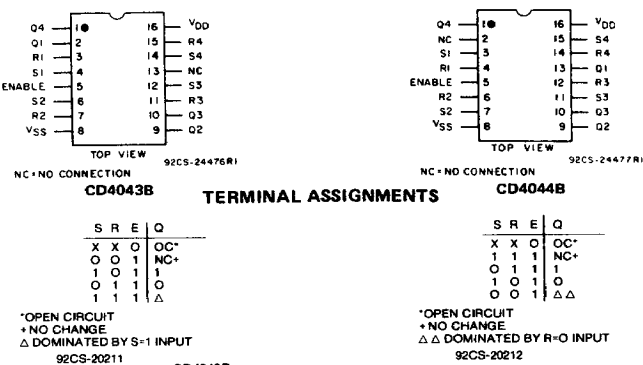


Fig. 1 — Logic diagrams.



MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})	-0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5 to $V_{DD} + 0.5$ V
DC INPUT CURRENT, ANY ONE INPUT	± 10 mA
POWER DISSIPATION PER PACKAGE (P_D):	
For $T_A = -40$ to $+60^\circ\text{C}$ (PACKAGE TYPE E)	500 mW
For $T_A = +60$ to $+85^\circ\text{C}$ (PACKAGE TYPE E)	Derate Linearly at 12 mW/ $^\circ\text{C}$ to 200 mW
For $T_A = -55$ to $+100^\circ\text{C}$ (PACKAGE TYPES D, F, K)	500 mW
For $T_A = +100$ to $+125^\circ\text{C}$ (PACKAGE TYPES D, F, K)	Derate Linearly at 12 mW/ $^\circ\text{C}$ to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR:	
For $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE}$ (All Package Types)	100 mW
OPERATING-TEMPERATURE RANGE (T_A):	
PACKAGE TYPES D, F, K, H	-55 to $+125^\circ\text{C}$
PACKAGE TYPE E	-40 to $+85^\circ\text{C}$
STORAGE TEMPERATURE RANGE (T_{stg})	-65 to $+150^\circ\text{C}$
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 inch (1.59 $\pm$ 0.79 mm) from case for 10 s max.	$+265^\circ\text{C}$

TRUTH TABLES

Recommended Operating Conditions $T_A = 25^\circ\text{C}$
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges.

Characteristic	V_{DD} (V)	Min.	Max.	Units
Supply-Voltage Range ($T_A = \text{Full Package Temperature Range}$)	—	3	18	V
SET or RESET Pulse Width, t_{pw}	5	160	—	ns
	10	80	—	
	15	40	—	

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STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C) Values at -55, +25, +125 Apply to D, F, K, H Packages Values at -40, +25, +85 Apply to E Package							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	+25							
				-55	-40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I _{DD} Max.	—	0,5	5	1	1	30	30	—	0.02	1	μA
	—	0,10	10	2	2	60	60	—	0.02	2	
	—	0,15	15	4	4	120	120	—	0.02	4	
	—	0,20	20	20	20	600	600	—	0.04	20	
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	—	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	—	
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—	
Output Voltage: Low-Level, V _{OL} Max.	—	0,5	5	0.05				—	0	0.05	V
	—	0,10	10	0.05				—	0	0.05	
	—	0,15	15	0.05				—	0	0.05	
Output Voltage: High-Level, V _{OH} Min.	—	0,5	5	4.95				4.95	5	—	V
	—	0,10	10	9.95				9.95	10	—	
	—	0,15	15	14.95				14.95	15	—	
Input Low Voltage, V _{IL} Max.	0.5, 4.5	—	5	1.5				—	—	1.5	V
	1, 9	—	10	3				—	—	3	
	1.5,13.5	—	15	4				—	—	4	
Input High Voltage, V _{IH} Min.	0.5, 4.5	—	5	3.5				3.5	—	—	V
	1, 9	—	10	7				7	—	—	
	1.5, 3.5	—	15	11				11	—	—	
Input Current I _{IN} Max.	—	0,18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA
3-State Output Leakage Current I _{OUT} Max.	0,18	0,18	18	±0.4	±0.4	±12	±12	—	±10 ⁻⁴	±0.4	μA

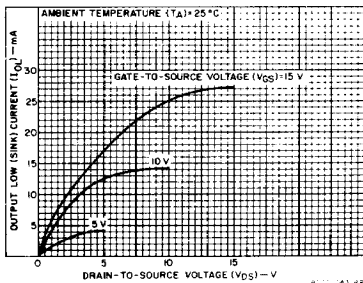


Fig. 2 — Typical output low (sink) current characteristics.

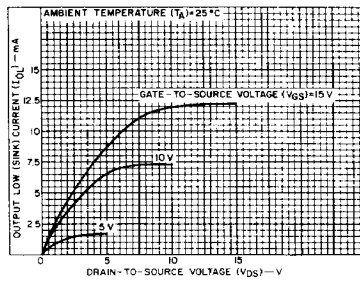


Fig. 3 — Minimum output low (sink) current characteristics.

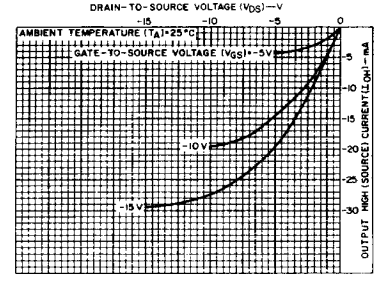


Fig. 4 — Typical output high (source) current characteristics.

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DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}\text{C}$; Input $t_r, t_f = 20\text{ ns}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$

CHARACTERISTIC	V_{DD} (V)	LIMITS ALL TYPES		UNITS
		TYP.	MAX.	
Propagation Delay Time: t_{PHL}, t_{PLH} SET or RESET to Q	5 10 15	150 70 50	300 140 100	ns
3-State Propagation Delay Time: ENABLE to Q t_{PHZ}, t_{PZH}	5 10 15	115 55 40	230 110 80	ns
t_{PLZ}, t_{PZL}	5 10 15	90 50 35	180 100 70	ns
Transition Time: t_{THL}, t_{TLH}	5 10 15	100 50 40	200 100 80	ns
Minimum SET or RESET Pulse Width, t_W	5 10 15	80 40 20	160 80 40	ns
Input Capacitance, (Any Input) C_{IN}	—	5	7.5	pF

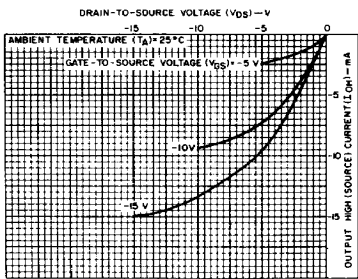


Fig. 5 — Minimum output high (source) current characteristics.

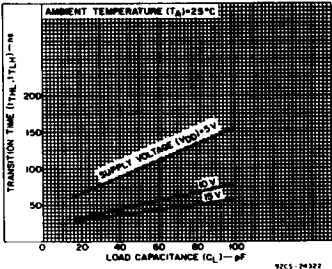


Fig. 6 — Typical transition time vs. load capacitance.

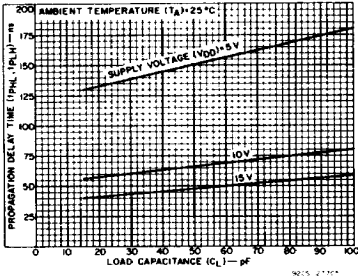


Fig. 7 — Typical propagation delay time vs. load capacitance—SET, RESET to Q, $\bar{Q}$.

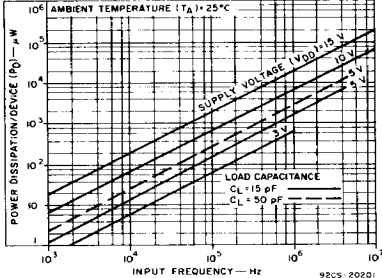


Fig. 8 — Typical power dissipation vs. frequency.

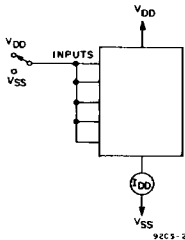


Fig. 9 — Quiescent device current.

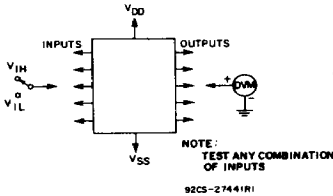


Fig. 10 — Input voltage.

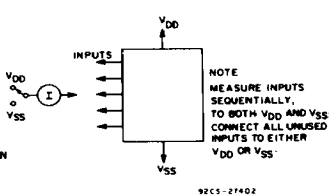


Fig. 11 — Input current.

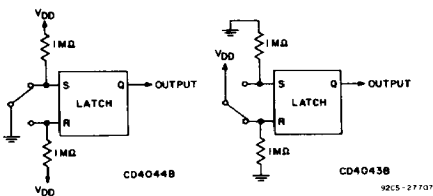
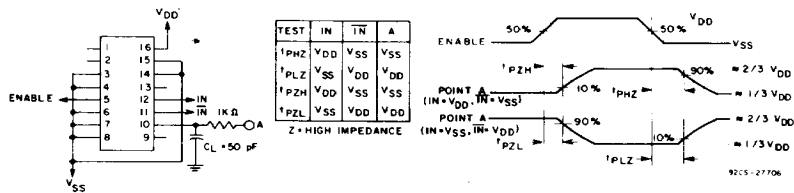


Fig. 12 — Switch bounce eliminator.

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CHIP PHOTOGRAPHS
DIMENSIONS AND PAD LAYOUTS

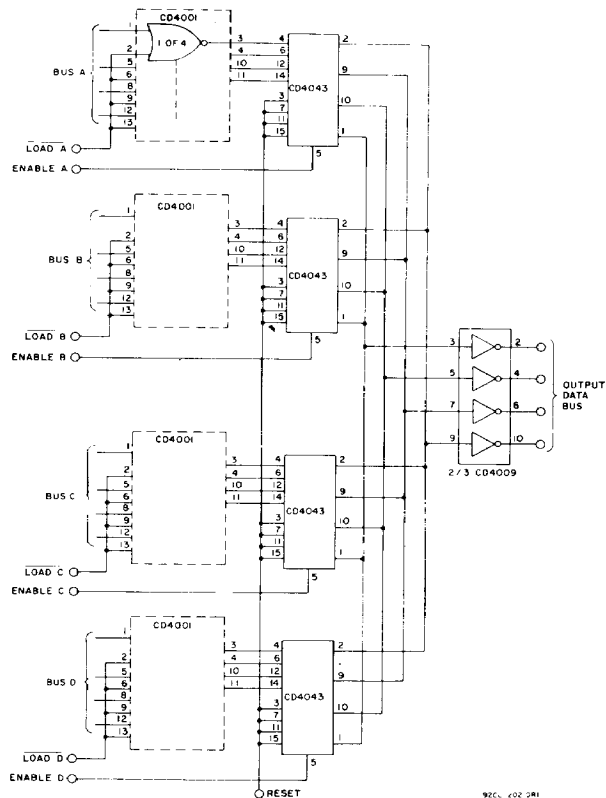
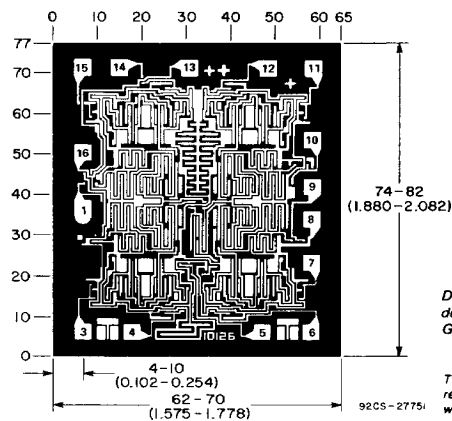
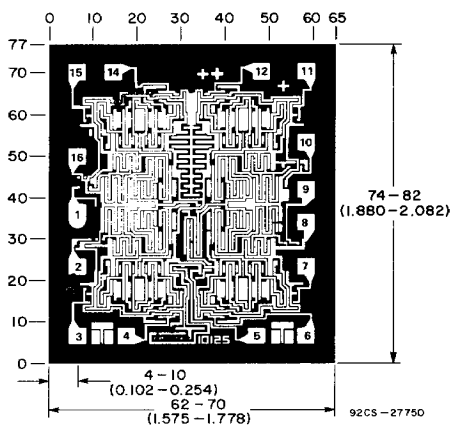


Fig. 14 - Multiple bus storage.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of -3 mils to +16 mils applicable to the nominal dimensions shown.